

Electronic Supplementary Information (ESI)

Cu-NHC based phosphorescent binuclear Iridium(III)/Copper(I) complex with an unpredictable near-linear two-coordination mode

Chao Shi,^{a,b} Manli Huang,^c Qiuxia Li,^a Guohua Xie,^c Chuluo Yang*^c and Aihua Yuan*^{a,b}

Contents:

Synthesis.....	S2
X-ray crystal structure analysis.....	S3
Photophysical properties.....	S4
OLED Device characterization.....	S6
DFT calculation.....	S7
NMR spectra.....	S8
References.....	S10

Synthesis

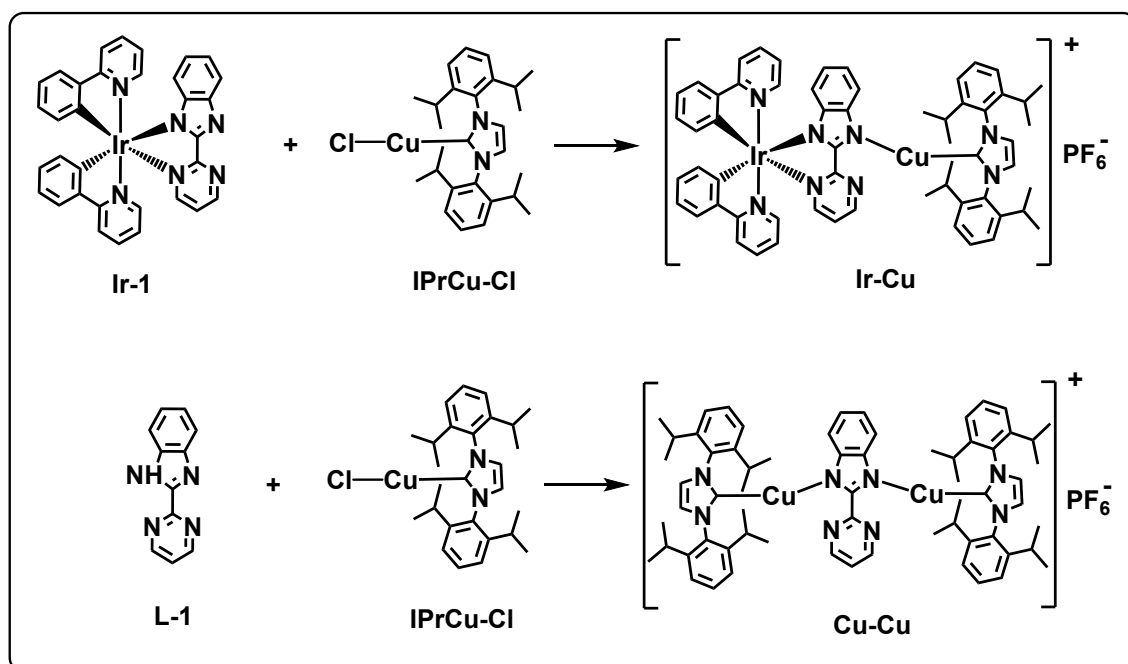


Fig. S1. The synthetic routes for binuclear Iridium(III)/Copper(I) complex **Ir-Cu** and Copper(I)/Copper(I) complex **Cu-Cu**.

X-ray crystal structure analysis

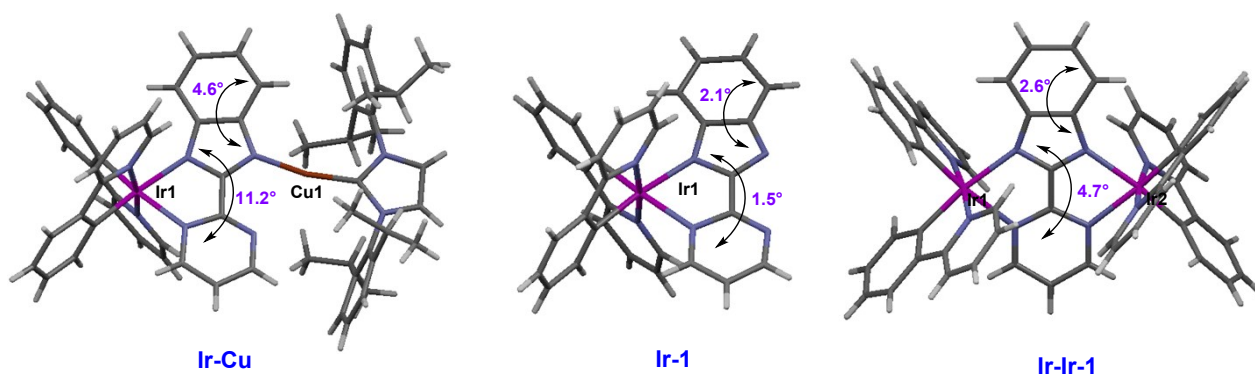


Fig. S2. The dihedral angles comparisons for ligand L-1 in complex Ir-Cu, Ir-1 and Ir-Ir-1.

Table S1. Crystallographic Data for Ir-Cu

Complex	Ir-Cu
chemical formula	C ₆₀ H ₅₉ CuIrN ₈ F ₆ P
formula weight	1292.86
crystal size (mm)	0.18 × 0.21 × 0.23
temperature (K)	291
radiation	0.71073
crystal system	Triclinic
space group	P-1
a(Å)	13.565(2)
b(Å)	14.327(2)
c(Å)	17.823(2)
α(°)	70.405(3)
β(°)	69.494(2)
γ(°)	62.654(2)
V(Å ³)	2817.7(7)
Z	2
ρ _(calc) (g/cm ³)	1.524

F (000)	1300
absorp.coeff. (mm ⁻¹)	2.831
θ range (deg)	1.6 to 27.7
reflins collected	56406 ($R_{\text{int}} = 0.040$)
indep. reflins	13006
Refns obs. [$I > 2\sigma(I)$]	9742
data/restr/paras	13006/0/701
GOF	1.04
R_1/wR_2 [$I > 2\sigma(I)$]	0.0549/0.0808
R_1/wR_2 (all data)	0.0838/0.0864
larg peak and hole(e/Å ³)	2.31/-1.21

Photophysical properties

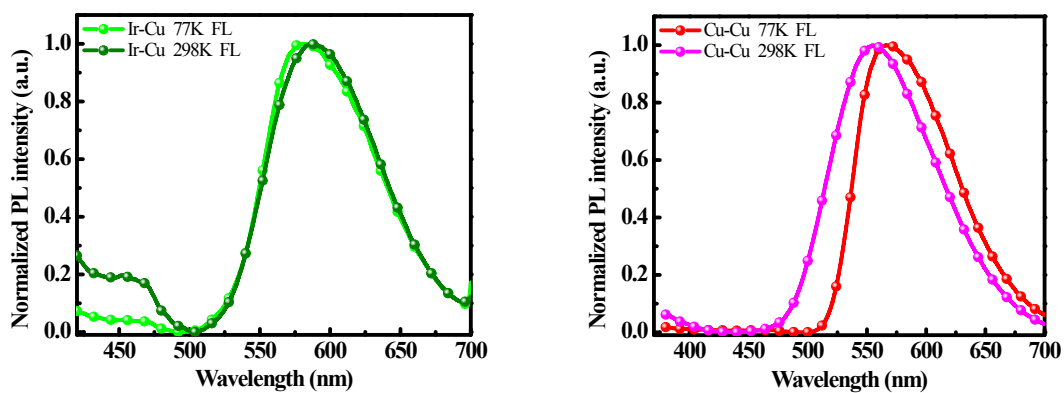


Fig. S3. PL spectrum comparison for Ir-Cu and Cu-Cu at different temperatures.

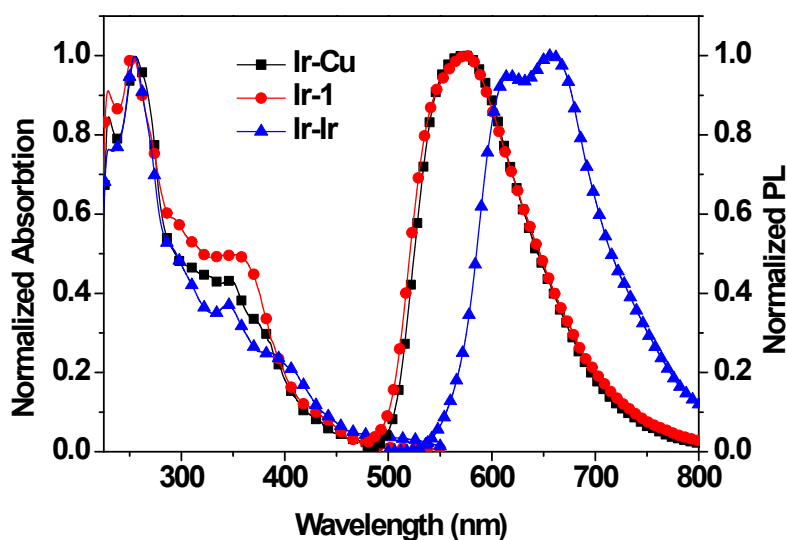


Fig. S4. UV absorption and PL spectrum of **Ir-Cu**, **Ir-1** and **Ir-Ir** in CH_2Cl_2 solution at room temperatures.

Table S2. Photophysical data comparison for **Ir-Cu**, **Ir-1** and **Ir-Ir**.

complex	$\lambda_{\text{abs}}^{[a]}$ nm (log ϵ)	PL ^[a] (nm)	$\Phi_{\text{PL}}^{[a]}$ (%)	$\tau^{[a]}$ (ns)
Ir-Cu	230(4.57), 294(4.44), 374(4.09), 450(3.16),	252(4.65), 304(4.45), 338(4.37), 420(3.62), 500(2.63)	575	21
	230(4.95), 290(4.79), 374(4.41), 450(3.41),	251(5.03), 304(4.80), 339(4.71), 420(3.90), 500(2.84)	574	29
	230(4.54), 290(4.39), 374(4.04), 450(3.12),	251(4.61), 304(4.40), 339(4.32), 420(3.57), 500(2.60)	619,659	35
				806

^[a] Measured in degassed CH_2Cl_2 at a concentration of 10^{-4} M, and log ϵ values are shown in parentheses at 298 K. The excitation wavelength is 370 nm.

OLED Device characterization

The prepatterned indium tin oxide (ITO) substrates were cleaned by ultrasonic acetone bath, followed by ethanol bath. Afterwards, the substrates were dried with N₂ and then loaded into a UV-Ozone chamber. After UV-Ozone treatment, The PEDOT: PSS layer was spin-coated on the ITO substrate as the hole-injecting layer, and then annealed at 120 °C for 10 min inside the N₂-filled glove-box. The emitter layer was also prepared by spin-coating directly on the hole-injecting layer, and then annealed at 50 °C for 10 min. The electron-transporting material and the cathode material were thermally evaporated onto the emitter layer in a vacuum chamber. Before taken out of the glove-box, the devices were encapsulated with UV-curable epoxy. The voltage-current-luminance characteristics and the EL spectra were simultaneously measured with PR735 SpectraScan Photometer and Keithley 2400 sourcemeter unit under ambient atmosphere at room temperature.

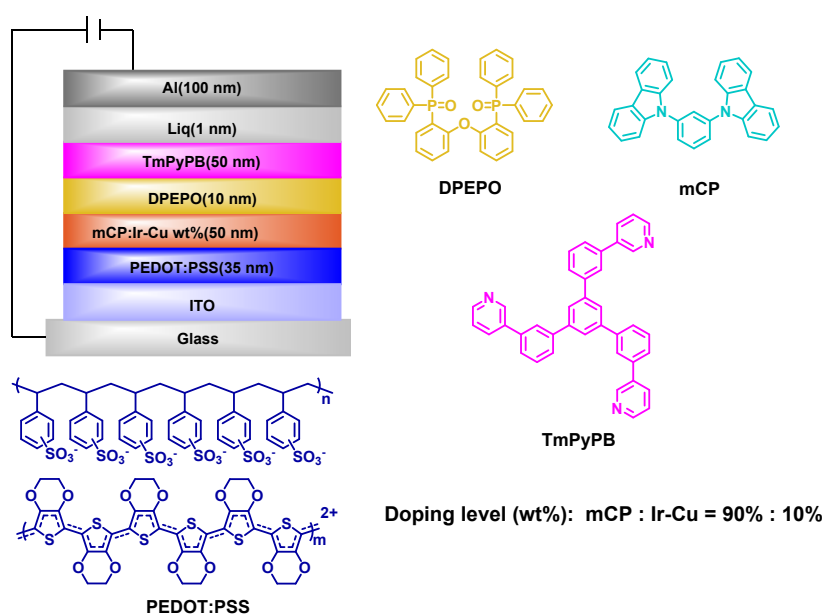


Fig. S5. Configuration of the OLEDs and chemical structures for the materials involved.

Table S3. EL performances of the device for Ir-Cu.

complex	V_{on}^a [V]	$EQE_{max}/CE_{max}/PE_{max}^b$ [%/cd A ⁻¹ /lm W ⁻¹]	λ_{ems}^c [nm]	CIE ^d (x, y)
Ir-Cu	8	2.6/7.4/1.2	590	(0.49, 0.48)

^a Voltage in the luminance of 10 cd/m². ^b Maximum external quantum efficiency (EQE_{max}), maximum current efficiency (CE_{max}), maximum power efficiency (PE_{max}). ^c Maximum emission wavelength of the EL spectra. ^d The Commission Internationale de l'Eclairage (CIE) coordinates.

DFT calculation

DFT method was used to optimize the geometries all the complexes. The electronic transition energies and electron correlation effects were also calculated by (TD)-DFT method with the B3LYP functional (TD-B3LYP). The LANL2DZ basis set was used to treat with the iridium atom and copper, and the 6-31G (d) basis set was used to treat with all other atoms. All calculations were carried out according to the Gaussian 09 program.¹

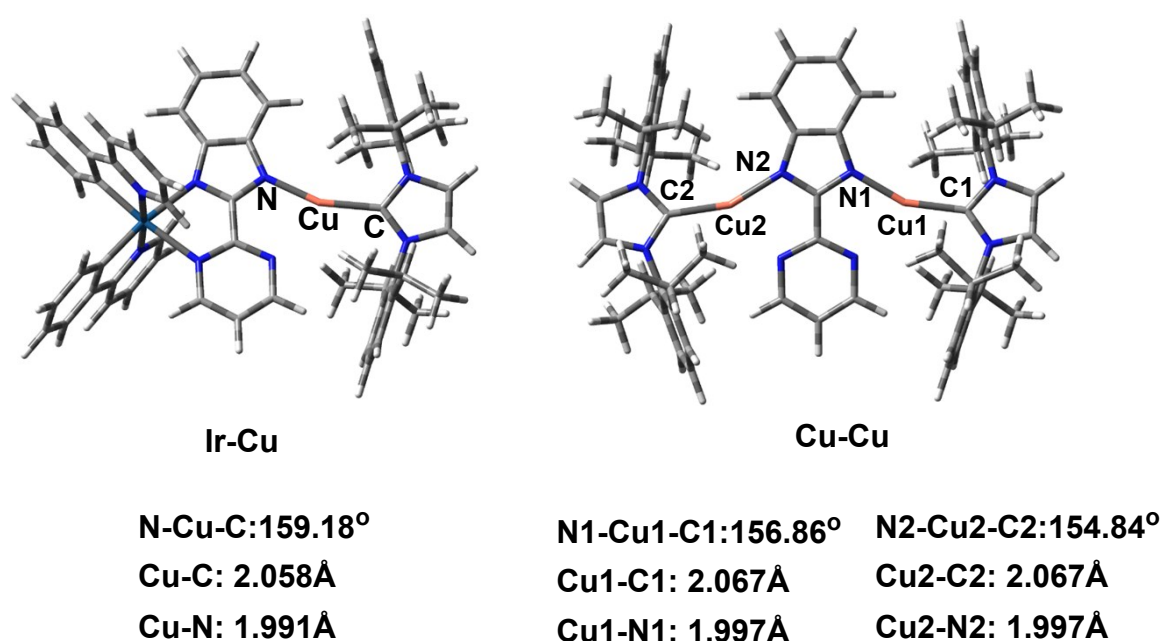


Fig. S6. Calculated optimized structure for Ir-Cu and Cu-Cu.

Table S4. Calculated energies and oscillator strengths for lowest-energy singlet (S₁) and triplet (T₁) transitions.

complexes	states	E (eV)	Oscillator strength	main configurations (CI coeff)	Character
Ir-Cu	S ₁	2.42	0.0001	HOMO→LUMO (0.65)	MLCT/LLCT
	T ₁	2.32	0	HOMO-1→LUMO (0.57) HOMO→LUMO (0.36)	³ ILCT/ ³ MLCT/ ³ LLCT
Cu-Cu	S ₁	2.90	0	HOMO-2→LUMO (0.70)	ILCT/MLCT
	T ₁	2.58	0	HOMO→LUMO (0.67)	³ ILCT/ ³ MLCT

NMR spectra

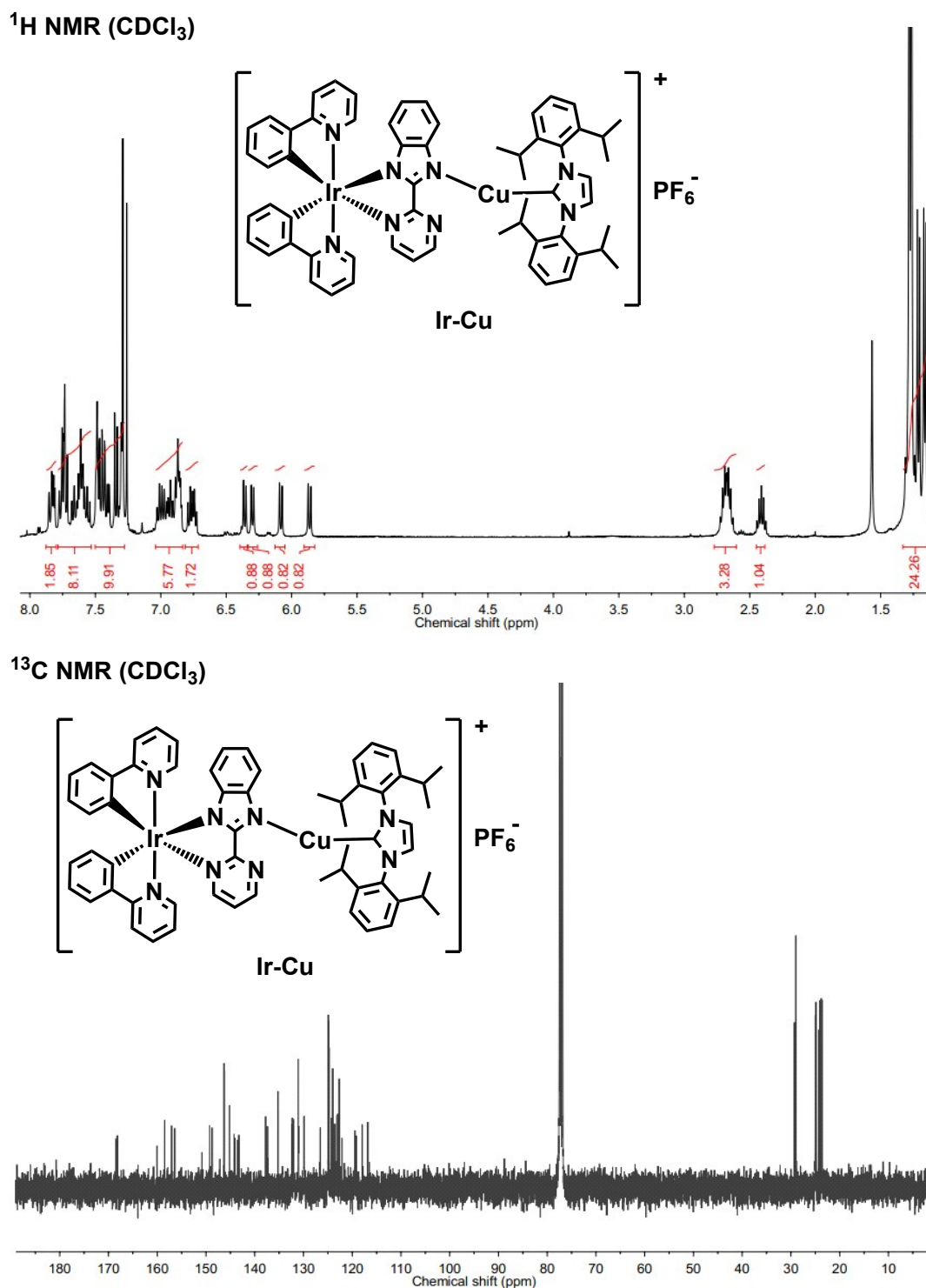
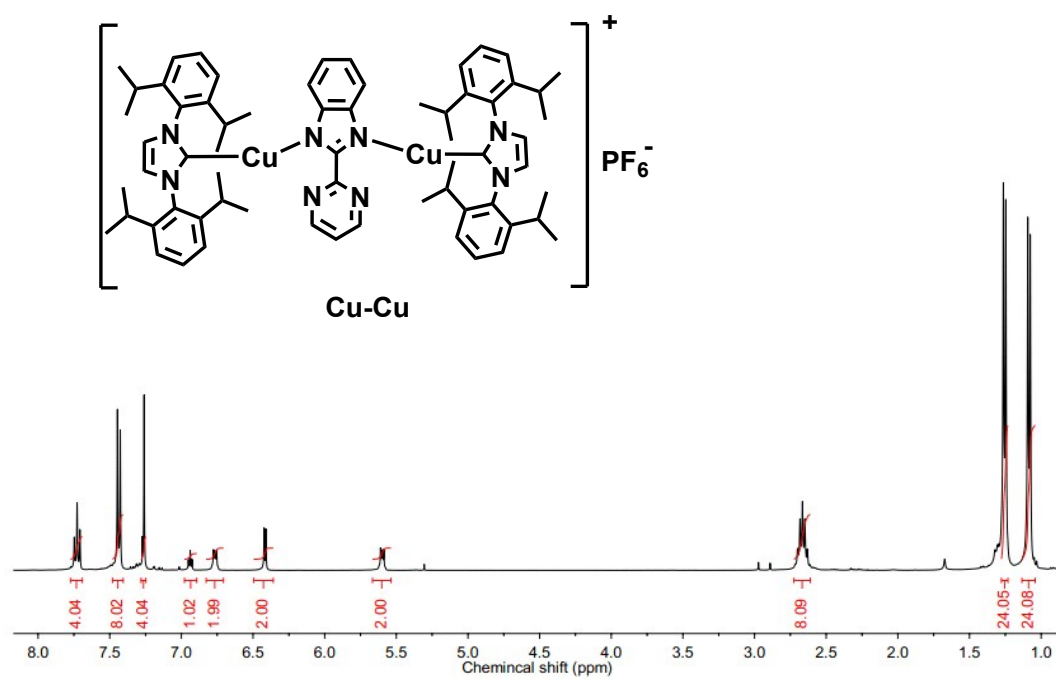


Fig. S7. ¹H NMR and ¹³C NMR spectra of Ir-Cu.

^1H NMR (CDCl_3)



^{13}C NMR (CDCl_3)

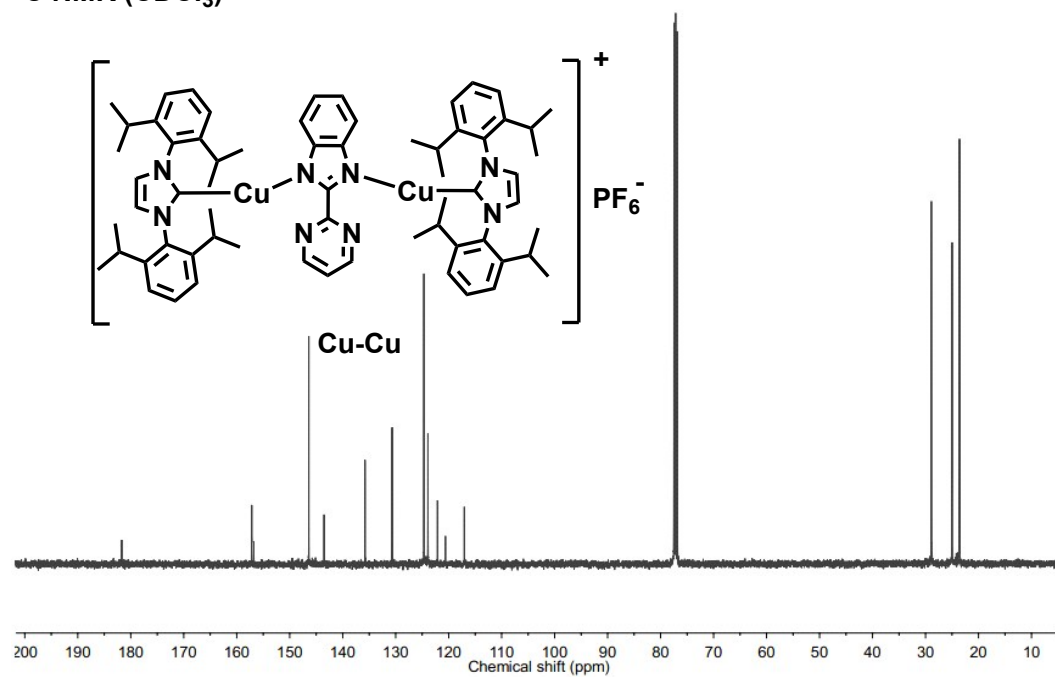


Fig. S8. ^1H NMR and ^{13}C NMR spectra of Cu-Cu .

References

1. M. J. Frisch, G. W. Trucks, H. B. Schlegel, G. E. Scuseria, M. A. Robb, J. R. Cheeseman, G. Scalmani, V. Barone, B. Mennucci, G. A. Petersson, H. Nakatsuji, M. Caricato, X. Li, H. P. Hratchian, A. F. Izmaylov, J. Bloino, G. Zheng, J. L. Sonnenberg, M. Hada, M. Ehara, K. Toyota, R. Fukuda, J. Hasegawa, M. Ishida, T. Nakajima, Y. Honda, O. Kitao, H. Nakai, T. Vreven, J. A. Montgomery Jr., J. E. Peralta, F. Ogliaro, M. Bearpark, J. J. Heyd, E. Brothers, K. N. Kudin, V. N. Staroverov, T. Keith, R. Kobayashi, J. Normand, K. Raghavachari, A. Rendell, J. C. Burant, S. S. Iyengar, J. Tomasi, M. Cossi, N. Rega, J. M. Millam, M. Klene, J. E. Knox, J. B. Cross, V. Bakken, C. Adamo, J. Jaramillo, R. Gomperts, R. E. Stratmann, O. Yazyev, A. J. Austin, R. Cammi, C. Pomelli, J. W. Ochterski, R. L. Martin, K. Morokuma, V. G. Zakrzewski, G. A. Voth, P. Salvador, J. J. Dannenberg, S. Dapprich, A. D. Daniels, O. Farkas, J. B. Foresman, J. V. Ortiz, J. Cioslowski and D. J. Fox, Gaussian 09, Revision B.01, Gaussian, Inc., Wallingford CT, **2010**.